

0998303.120301
FOE021" FOE8660

UNITED STATES PATENT APPLICATION
FOR
METHOD FOR FORMING CONTACT HOLE AND SPACER OF
SEMICONDUCTOR DEVICE
BY
SUNG-CHAN PARK, PHIL-GOO KONG, AND KUK-HAN YOON

DESCRIPTION OF THE INVENTION

Field of the Invention

The present invention relates to semiconductor devices; more particularly, to methods for forming a contact hole for reducing parasitic capacitance between conductive layer patterns, preventing bad contact caused by a mask misalignment, and effectively filling an interlayer insulating layer between the conductive patterns.

DESCRIPTION OF THE RELATED ART

With increases in integration of semiconductor devices, a self-align contact (hereinafter, referred to as a SAC) etching method has been used in a conventional storage node contact process.

Hereinafter, problems with a conventional contact hole forming method will be described in detail referring to the accompanying drawings.

A method for forming a conventional contact hole for a storage node contact using a mask (M1) that defines a contact hole 10, as shown in Fig. 1, is described with reference to Figs. 2A to 2E.

As shown in Fig. 2A, a conductive layer 21 and a mask layer 22 for a bit line are formed with tungsten on a semiconductor substrate 20 where a lower structure formation is completed, and first photoresist patterns 23 which define a bit line pattern are formed on mask layer 22. Mask layer 22 is used for protecting a bit line in a contact hole forming

process by etching an interlayer oxide layer, and is formed of a nitride layer which has a different etching rate than an oxide layer.

Subsequently, mask layer 22 and conductive layer 21 are selectively etched by using first photoresist layer patterns 23 as etching masks. First photoresist layer patterns 23 are removed after forming mask patterns 22A and bit lines 21A, as shown in Fig. 2B.

As shown in Fig. 2C, spacers 24 are formed on sidewalls of the mask patterns 22A and the bit lines 21A. Spacers 24 are used as insulation between bit lines 21A, and are formed by depositing a nitride layer and by applying a blanket etching process to the deposited nitride. Preferably, the deposited nitride for spacers 24 is selected based on an etching rate required to form contact holes with an etchant. Typically, such a selective etching rate is obtained between a nitride layer and an oxide layer.

As shown in Fig. 2D, an interlayer oxide layer 25 is formed on the resulting structure, and second photoresist patterns 26, which define the contact hole forming regions, are formed on interlayer oxide layer 25 by using a mask as shown in Fig. 1.

As shown in Fig. 2E, interlayer oxide layer 25 is etched by using second photoresist patterns 26 as etching masks, thereby to form contact holes 10 that expose contact regions between spacers 24, i.e., semiconductor substrate 20.

When the aforementioned SAC etching method using a contact hole mask is performed in a high integration device manufacturing process, photomask misalignment can result. As shown in Fig. 3A, if the photomask is deviated from its course, causing a misalignment of photoresist pattern 26A which defines the contact hole, the etching process is terminated on mask layer 22A and spacer 24, and a bottom portion of contact hole 10 is exposed badly, shown at 'A' in Fig. 3B. With highly integrated capacitor devices having narrow gaps between bit lines 21A, the problems caused by the misalignment become serious.

To prevent misalignment of a mask, a contact hole mask in the shape of a straight line is provided instead of a hole shape.

A conventional straight line shape of a storage node contact hole formation method using a straight line shape of mask M2, which is parallel to a word line WL and vertical to a bit line BL, is shown in Fig. 4, and cross-sectional views taken along the broken line B-B' are described in to Figs. 5A to 5E.

As shown in Fig. 5A, a conductive layer 51, such as a tungsten layer, and a mask layer 52 for forming a bit line are, in this order, formed on a semiconductor substrate 50 where a predetermined lower structure is completed. Then, first photoresist patterns 53, which define a bit line pattern, are formed on mask layer 52. Mask layer 52 is used to protect the bit line when etching an interlayer insulating

oxide layer to form contact holes. Mask layer 52 is formed with a nitride layer which is different from an oxide layer with regard to their etching rates.

Mask layer 52 and conductive layer 51 are selectively etched by using first photoresist layer patterns 53 as etching masks. First photoresist layer patterns 53 are removed with the formation of mask nitride patterns 52A and bit lines 51A, as shown in Fig. 5B.

Referring to Fig. 5C, spacers 54 are formed on sidewalls of mask nitride patterns 52A and bit lines 51A, and an interlayer insulation oxide layer 55 is formed on the resulting structure. Spacers 54 are used as insulation between the neighboring bit lines 51A. Spacers 54 are formed by applying a blanket etching process to a nitride layer which is different from an oxide layer with regard to their etching rates.

Referring to Fig. 5D, a second photoresist layer pattern 56 defining a contact hole region by using the straight line shape of mask (M2), as shown in Fig. 4, is formed on interlayer insulation oxide layer 55.

Subsequently, referring to Fig. 5E, interlayer insulating oxide layer 55 is etched by using second photoresist layer pattern 56 as an etching mask to form contact regions between spacers 54, for example, whereby contact holes which expose semiconductor substrate 50 are formed.

The straight line shaped mask has a larger overlap margin than the hole shape mask so that mask misalignment problems

may be solved. However, bad filling problems of the high density plasma (HDP) oxide layer which forms the interlayer insulating layer may not be solved.

The more the integration of devices is increased, the narrower a conductive layer pattern gap is, so that gap-fill characteristics of an interlayer insulating layer worsen.

With progress in integration, the gap between the bit lines narrows so that the HDP oxide layer, which forms the interlayer insulating layer, may not fill the gap between the bit lines. This filling problem in the interlayer oxide layer is brought out as shown in Fig. 6. That is, voids V are generated within HDP oxide layer 65 between sidewall spacers 64 of neighboring bit lines 61A. In Fig. 6, reference numerals 60 and 62A denote a semiconductor substrate and mask patterns, respectively.

In the HDP oxide layer, when the aspect ratio of the void is over 4.0, that is, when the height of void is four times or more greater than the width thereof, voids are generated. To solve the problem caused by bad filling of the interlayer insulating layer, a conventional pre-polysilicon plug (hereinafter, referred to as a PPP) forming method has been used and will be described in detail below.

First, as shown in Fig. 7A, bit lines 71, mask patterns 72, and spacers 73 are formed on a semiconductor substrate 70 having a predetermined bottom structure, and a polysilicon layer 74 is formed on the resulting structure.

As shown in Fig. 7B, the polysilicon layer is subjected to an etch-back or polishing process until upper surfaces of mask patterns 72, which cover bit lines 71, are exposed, thereby forming PPP layers 74A.

As shown in Fig. 7C, an interlayer insulating layer 75 is formed on the resulting structure and photoresist patterns 76, which defines contact holes, are formed on interlayer insulating layer 75.

Subsequently, as shown in Fig. 7D, contact holes 77, which expose PPP layers 74A, are formed by selectively etching interlayer insulating layer 75 using photoresist pattern 76 as an etching mask, and then photoresist pattern 76 is removed.

The conventional PPP method may reduce the depth of a void so that an interlayer insulating layer is satisfactorily filled. However, the method may add processing steps such as a polysilicon layer deposition and an etch-back process.

The above-mentioned straight line shaped contact hole method and the PPP method may solve mask misalignment problems caused by contact hole formation in a hole shape, and void generation problems within the interlayer insulating layer, respectively. However, the above-mentioned methods may not solve increases in bit line parasitic capacitance.

When an electrical signal is applied to a specific bit line, parasitic capacitance induces an electrical signal in adjacent bit lines. This parasitic capacitance increases when bit lines are wrapped with a nitride layer, which has a large dielectric constant for the SAC etching. To solve the

layer patterns by selectively etching the interlayer insulating layer and, at the same time, forming a spacer leaving the interlayer insulating layer on the sidewall of the conductive layer patterns.

According to the present invention, an interlayer insulation layer is deposited just after forming a conductive layer pattern, such as a gate electrode and a bit line, and a contact hole is formed by carrying out an etching process through a mask pattern which defines at least one contact hole pattern selected from a group comprising a straight line shaped, a T-shaped pattern, and an I-shaped pattern, or forming an insulating spacer on sidewalls of the conductive layer patterns during a contact hole formation process, thereby forming contact holes and spacers between neighboring conductive layer patterns.

BRIEF DESCRIPTION OF THE DRAWINGS

Other features and aspects of the invention will become apparent from the following description of the embodiments with reference to the accompanying drawings, in which:

Fig. 1 is a plan view illustrating a conventional mask for forming a hole shape storage node contact hole;

Figs. 2A to 2E are cross-sectional views showing a conventional hole shaped storage node contact hole formation process;

Figs. 3A and 3B are cross-sectional views showing a problem of mask misalignment in a conventional hole shaped storage node contact hole formation process;

Fig. 4 is a plan view showing an arrangement of conventional straight line shaped storage node contact holes, bit lines and word lines;

Figs. 5A to 5E are perspective views showing a conventional straight line shaped storage node contact hole formation process;

Fig. 6 is a cross-sectional view showing voids generated within an interlayer insulating layer between neighboring bit lines in an interlayer insulating layer with a conventional semiconductor manufacturing process;

Figs. 7A to 7D are cross-sectional views showing a conventional pre-plug formation process; and

Figs. 8A to 8F are perspective views showing a straight line shaped storage node contact hole formation process in accordance with the present invention.

DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENTS

A semiconductor device manufacturing method according to the present invention will now be described in detail with reference to the accompanying drawings.

Figs. 8A to 8F are perspective views showing a straight line shaped storage node contact hole formation process in accordance with the present invention.

Referring to Fig. 8A, a conductive layer 81 for bit lines or gate electrodes is made of any one selected from the group consisting of W, WSi_x , $TiSi_x$, Al, and Cu and formed on a semiconductor substrate 80 where a predetermined lower structure, such as a well or a field oxide layer, is

completed. A mask layer 82 having a thickness of 400 Å to 5000 Å is formed on conductive layer 81, and first photoresist layer patterns 83, which define bit lines or gate electrode patterns, are formed. Mask layer 82 is used to protect the bit lines or gate electrode patterns. When contact hole formation is carried out by etching an interlayer insulating layer, mask layer 82 is formed of a nitride layer which is different from an oxide layer in their etching rates. For example, when the interlayer insulating layer is formed of an oxide layer, mask layer 82 is formed with SiN or SiON. When the interlayer insulating layer is formed with a polymer having a low dielectric constant layer, mask layer 82 is formed with oxide materials. It is possible to form mask layer 82 without relying on the etching characteristics of conductive layer 81.

Subsequently, mask nitride layer 82 and conductive layer 81 are selectively etched by using first photoresist layer patterns 83 as etching masks. Then the first photoresist layer patterns 83 are removed, thereby forming mask nitride layer patterns 82A and conductive layer patterns 81A, as shown in Fig. 8B.

Referring to Fig. 8C, an interlayer insulating layer 84 is formed on the resulting structure having a thickness of 500 Å to 10000 Å with an oxide layer or a low dielectric material which has a dielectric constant below 3.5, such as SiLK (a polymer produced by Dow Chemical Company), FLARE (a polymer produced by Honeywell International Inc.), FOX (a flowable

oxide by Dow Corning Corp.), Hydrogen silsesquioxane (HSQ), or benzocyclobutene (BCB).

Referring to Fig. 8D, a second photoresist layer pattern 85, which defines contact hole regions, is formed on interlayer insulating layer 84. Second photoresist layer pattern 85 is formed with a mask layer formed by a pattern selected from the group consisting of straight line shaped, a T-shaped, and an I-shaped patterns.

Next, interlayer insulating layer 84 is etched by using second photoresist layer pattern 85 as an etching mask, and second photoresist layer pattern 85 is then removed. According to the above-mentioned process, contact holes 88, which expose semiconductor substrate 80 are formed between neighboring conductive layer patterns 81A, as shown in Fig. 8E.

At this time, a plasma etching reactor having a high density greater than $10^{12}/\text{cm}^2$ or a middle density of $10^{11}/\text{cm}^2$ to $10^{12}/\text{cm}^2$ is used, and a pressure of the etching reactor may be 1 mTorr to 100 mTorr.

Where interlayer insulating layer 84 is an oxide layer, it is etched by a mixture of Ar, C, and F, such as a mixture gas of Ar/ C_4F_8 / CH_2F_2 , Ar/ C_4F_8 / O_2 , Ar/ C_4F_8 / CH_3F , Ar/ C_4F_8 / CHF_3 , or Ar/ C_5F_8 / O_2 . If interlayer insulating layer 84 is a polymer, it is etched by a mixed gas selected from Ar, O_2 , N_2 , H_2 , CH_4 , C_2H_4 , and C_xF_y .

Referring to Fig. 8F, spacers 86 are formed on sidewalls of mask pattern 82A and conductive layer patterns 81A. Spacers 86 are formed by depositing an insulating layer, such

substitutions are possible, without departing from the scope and spirit of the invention as set forth in the accompanying claims.

00000000-100001